

2019 26th International Workshop on Active-Matrix Flatpanel Displays and Devices (AM-FPD 2019)

**Kyoto, Japan
2 – 5 July 2019**



**IEEE Catalog Number: CFP1993R-POD
ISBN: 978-1-7281-1259-6**

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IEEE Catalog Number:	CFP1993R-POD
ISBN (Print-On-Demand):	978-1-7281-1259-6
ISBN (Online):	978-4-9908753-6-7

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H. Zuo¹, L. Zhang¹, Y. Yang¹, C. Fan¹, S. Zhang^{1,2}, ¹*Peking Univ., China*, ²*Active Matrix Display Beijing Engineering Res. Ctr., China*

— Coffee Break —

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Chairpersons : M. Kimura, *Ryukoku Univ., Japan*
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- 15 : 25 (5-3) (Withdrawn)

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